



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.  
TEL: 2790-0314 FAX: 2790-0206

High-speed double diode

BAV70

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

- High-speed switching in thick and thin-film circuits.

DESCRIPTION

The BAV70 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

MARKING

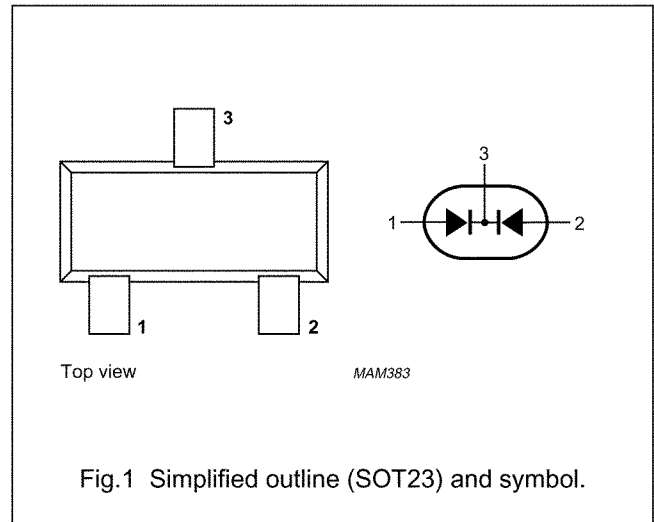
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAV70	A4*

Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

PINNING

PIN	DESCRIPTION
1	anode (a1)
2	anode (a2)
3	common cathode





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#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per diode</b>					
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	single diode loaded; note 1; see Fig.2	–	215	mA
		double diode loaded; note 1; see Fig.2	–	125	mA
$I_{FRM}$	repetitive peak forward current		–	450	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4			
		$t = 1\ \mu\text{s}$	–	4	A
		$t = 1\ \text{ms}$	–	1	A
		$t = 1\ \text{s}$	–	0.5	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

#### Note

1. Device mounted on an FR4 printed-circuit board.



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**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
<b>Per diode</b>				
$V_F$	forward voltage	see Fig.0		
		$I_F = 1\text{ mA}$	715	mV
		$I_F = 10\text{ mA}$	855	mV
		$I_F = 50\text{ mA}$	1	V
		$I_F = 150\text{ mA}$	1.25	V
$I_R$	reverse current	see Fig.5		
		$V_R = 25\text{ V}$	30	nA
		$V_R = 75\text{ V}$	2.5	$\mu\text{A}$
		$V_R = 25\text{ V}; T_j = 150\text{ }^\circ\text{C}$	60	$\mu\text{A}$
		$V_R = 75\text{ V}; T_j = 150\text{ }^\circ\text{C}$	100	$\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	1.5	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		360	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

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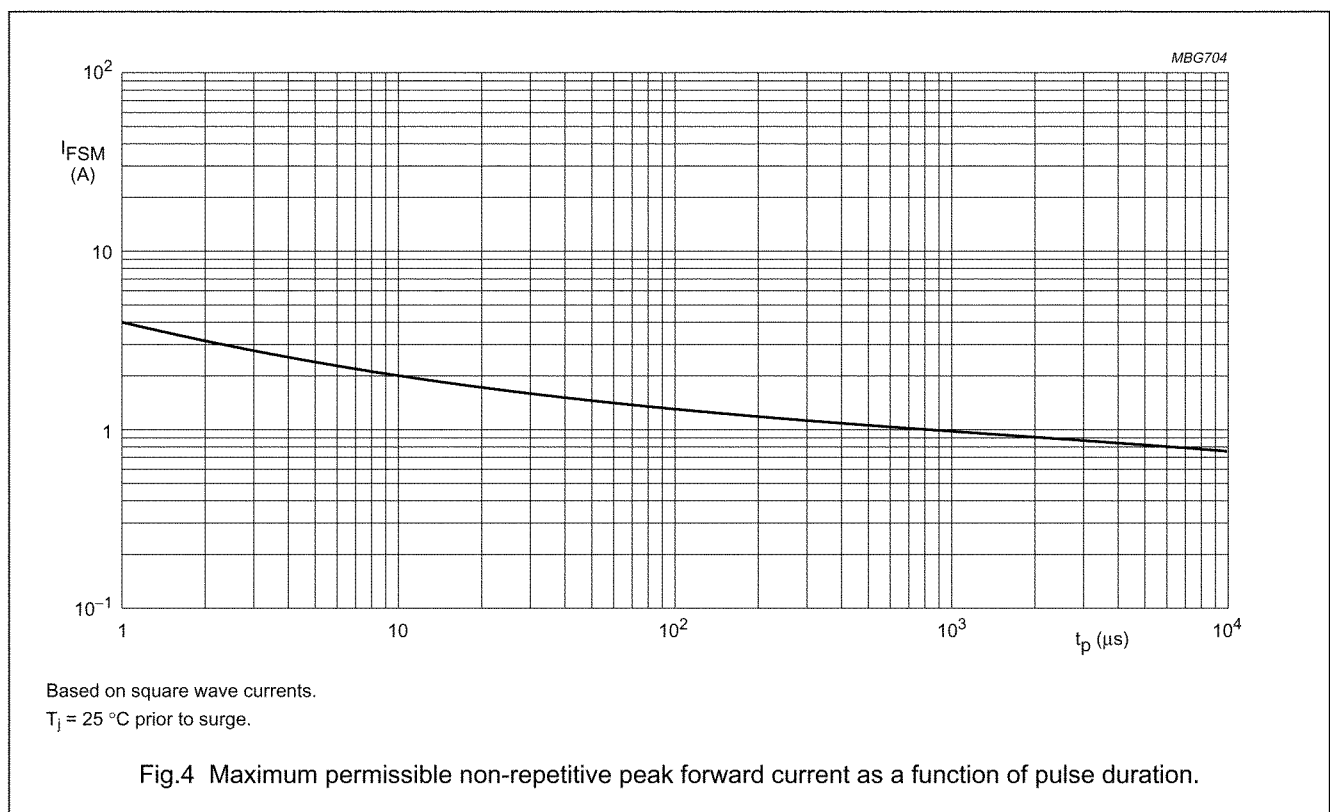
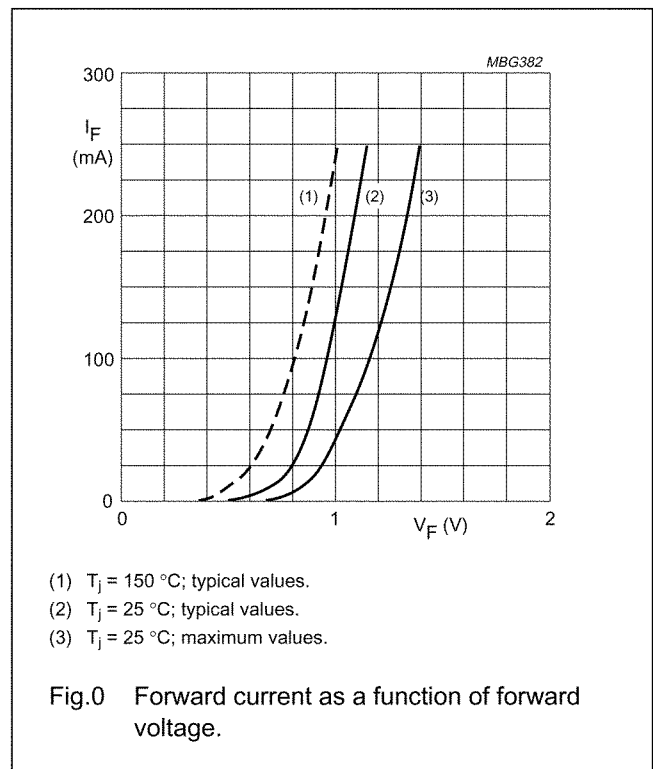
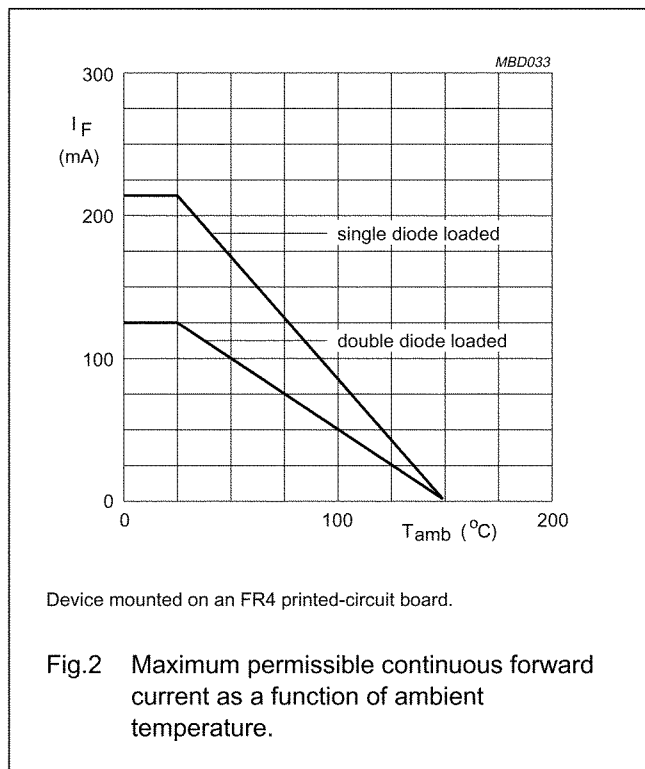
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GRAPHICAL DATA





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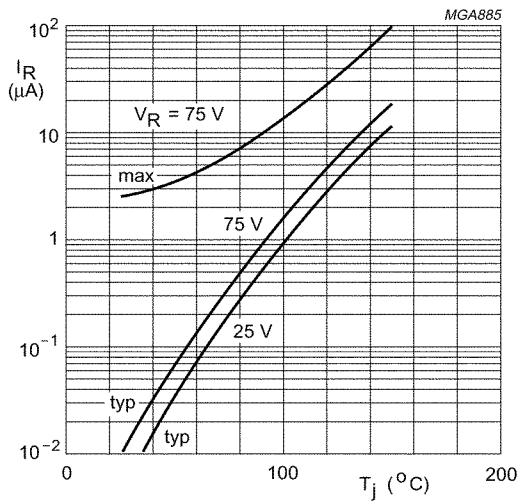
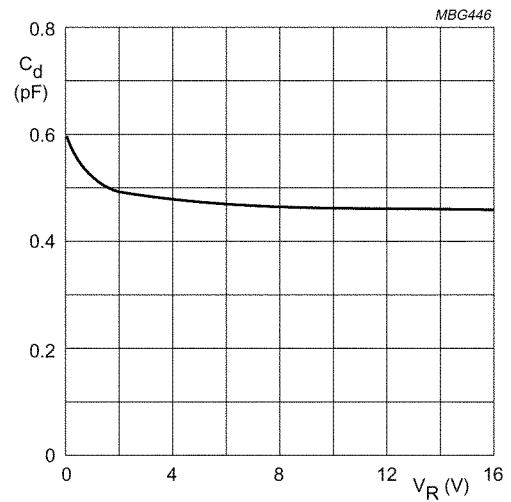


Fig.5 Reverse current as a function of junction temperature.



$f = 1\text{ MHz}; T_j = 25\text{ }^{\circ}\text{C}$ .

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



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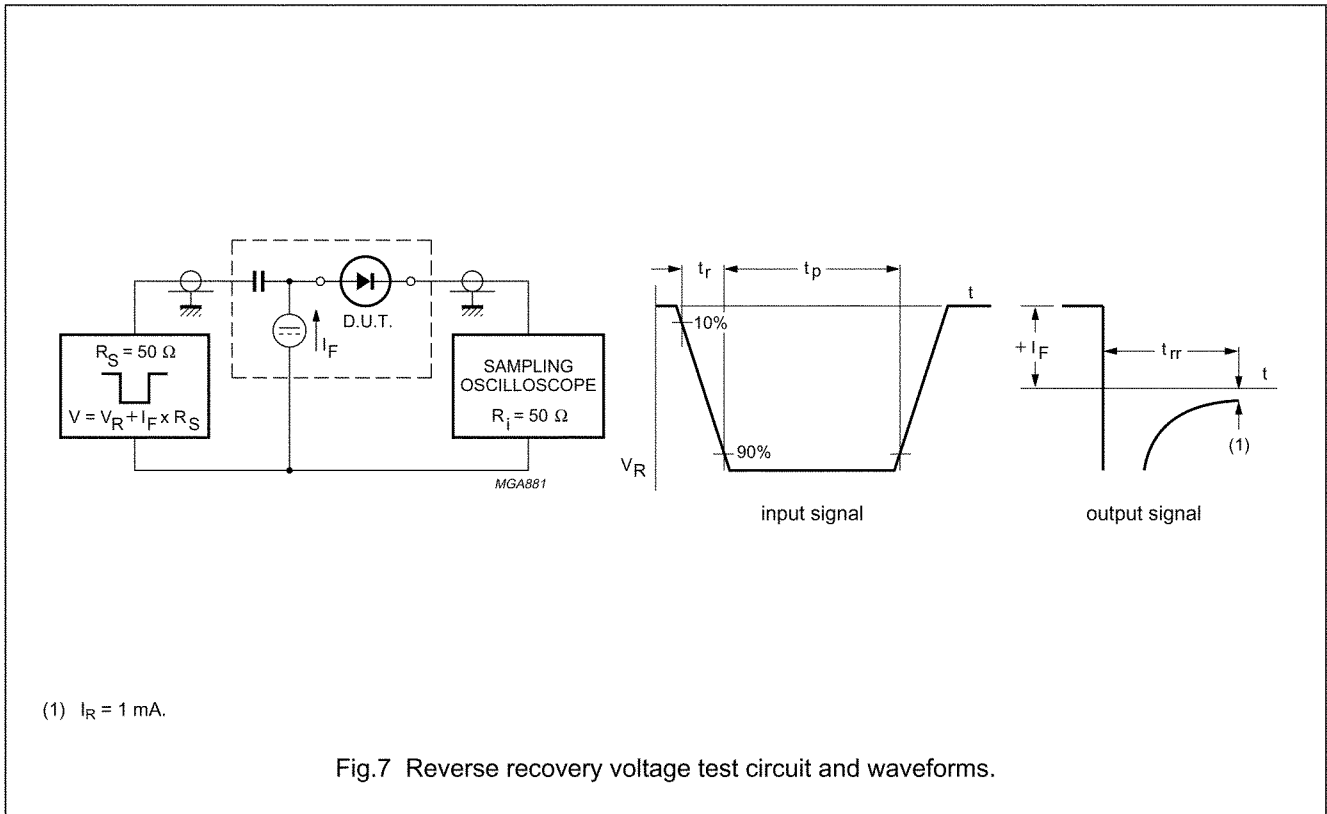


Fig.7 Reverse recovery voltage test circuit and waveforms.

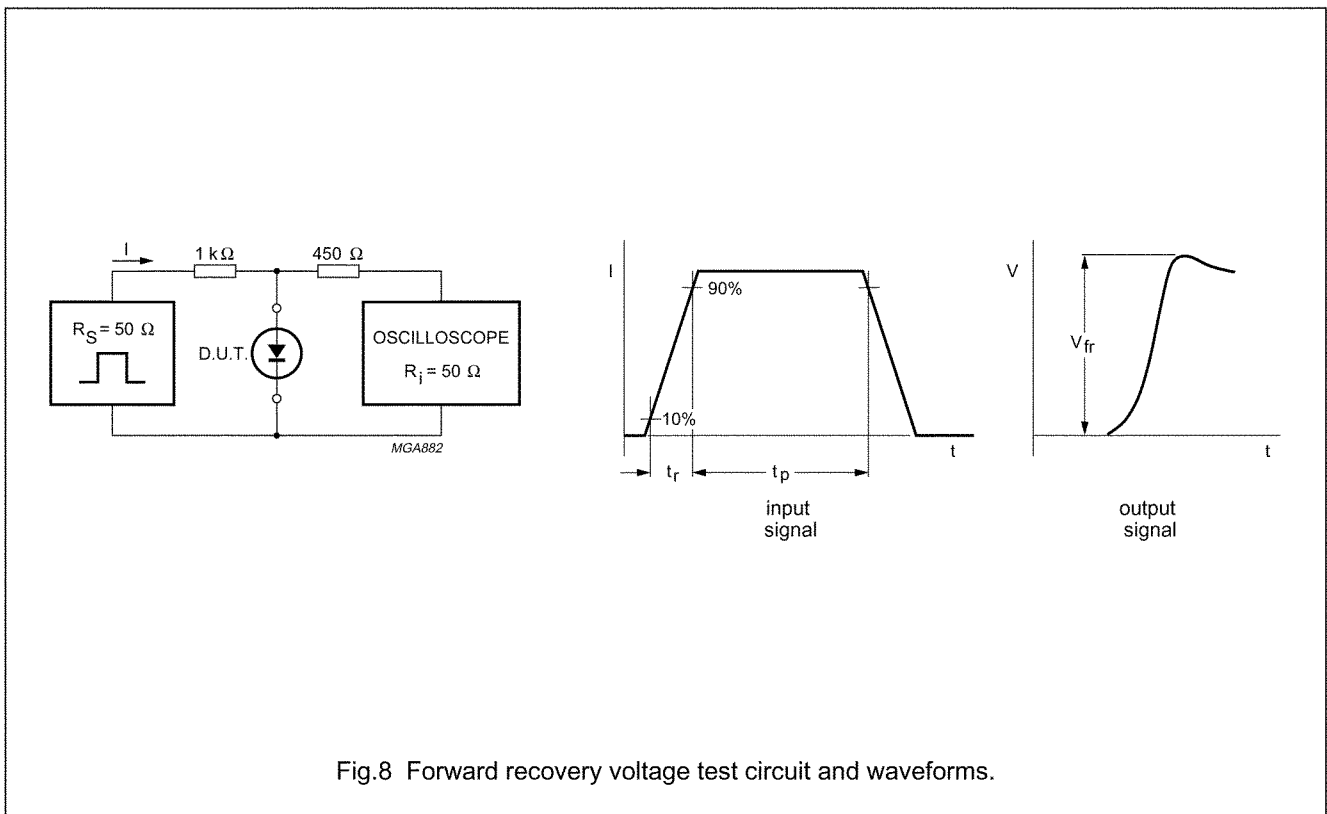


Fig.8 Forward recovery voltage test circuit and waveforms.



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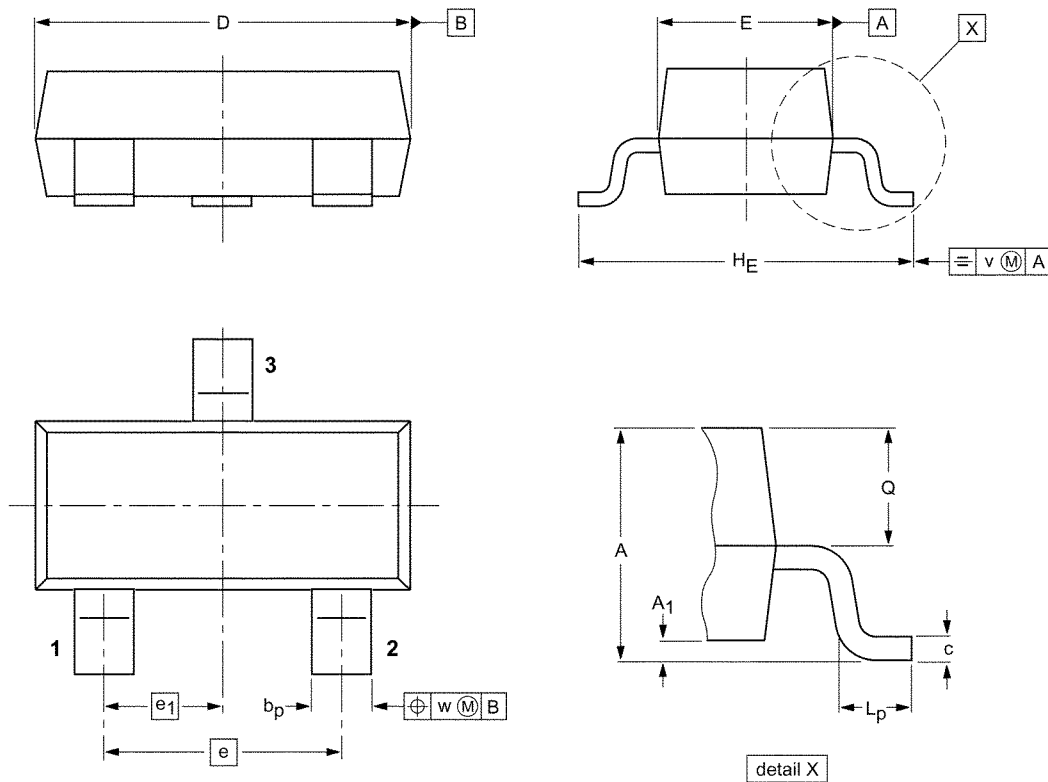
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				-97-02-28- 99-09-13